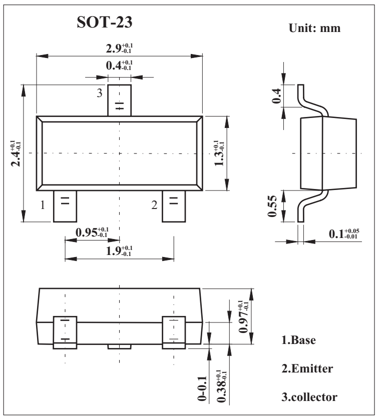
Silicon PNP Epitaxial

2SA1121

Features

- Low frequency amplifier



Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-35	V
Collector to emitter voltage	V_{CEO}	-35	V
Emitter to base voltage	V_{EBO}	-4	V
Collector current	I_C	-500	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = -10 mA, I_E = 0	-35			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -1 mA, R_{BE} = ∞	-35			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = -10 mA, I_C = 0	-4			V
Collector cutoff current	I_{CBO}	V_{CB} = -20 V, I_E = 0			-0.5	μA
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = -150 mA, I_B = -15 mA		-0.2	-0.6	V
DC current transfer ratio	h_{FE}	V_{CE} = -3 V, I_C = -10 mA	60		320	
Base to emitter voltage	V_{BE}	V_{CE} = -3 V, I_C = -10 mA		-0.64		V

h_{FE} Classification

Marking	SB	SC	SD
hFE	60～120	100～200	160～320